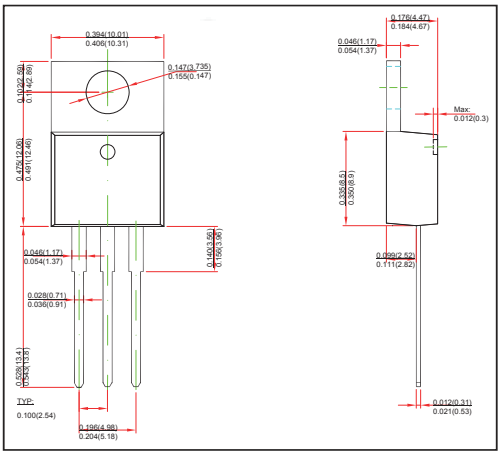
TO-220L Plastic-Encapsulate Transistors

FEATURES

- High Forward CurrentTransferRatio hFE which
- Has Satisfactory Linearity
- Low Collector to Emitter Saturation Voltage VcE(sat)
- Allowing Supply with the Radial Taping
- TRANSISTOR (NPN)

MECHANICAL DATA

- Case style:TO-220L molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I_C	3	A
Collector Power Dissipation	P_C	2	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 ~ +150	℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=0.1mA, I_E=0	80			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=30mA, I_B=0	80			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=0.1mA, I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=60V, I_E=0			100	μA
Collector cut-off current	I_{CEO}	V_{CE}=30V, I_B=0			100	μA
Emitter cut-off current	I_{EBO}	V_{EB}=6V, I_C=0			100	μA
DC current gain	$h_{FE(1)}$	V_{CE}=4V, I_C=1A	70		320	
	$h_{FE(2)}$	V_{CE}=4V, I_C=3A	10			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=3A, I_B=375mA			1.2	V
Base-emitter voltage	V_{BE}	V_{CE}=4V, I_C=3A			1.8	V
Transition frequency	f_T	V_{CE}=5V, I_C=0.2A, f=10MHz		30		MHz